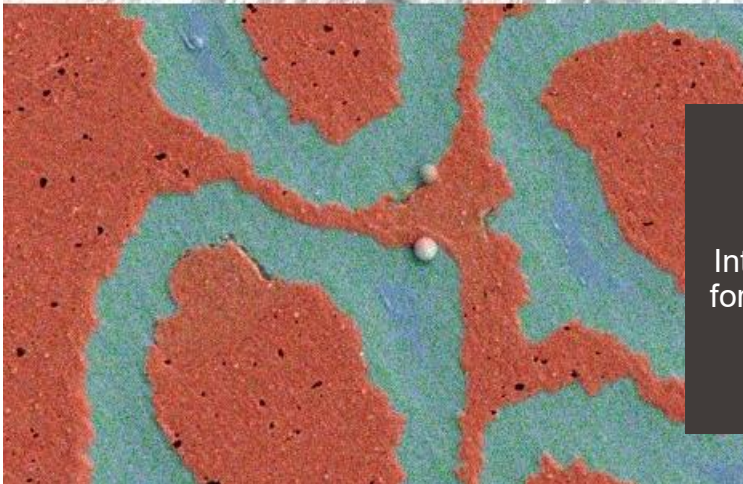
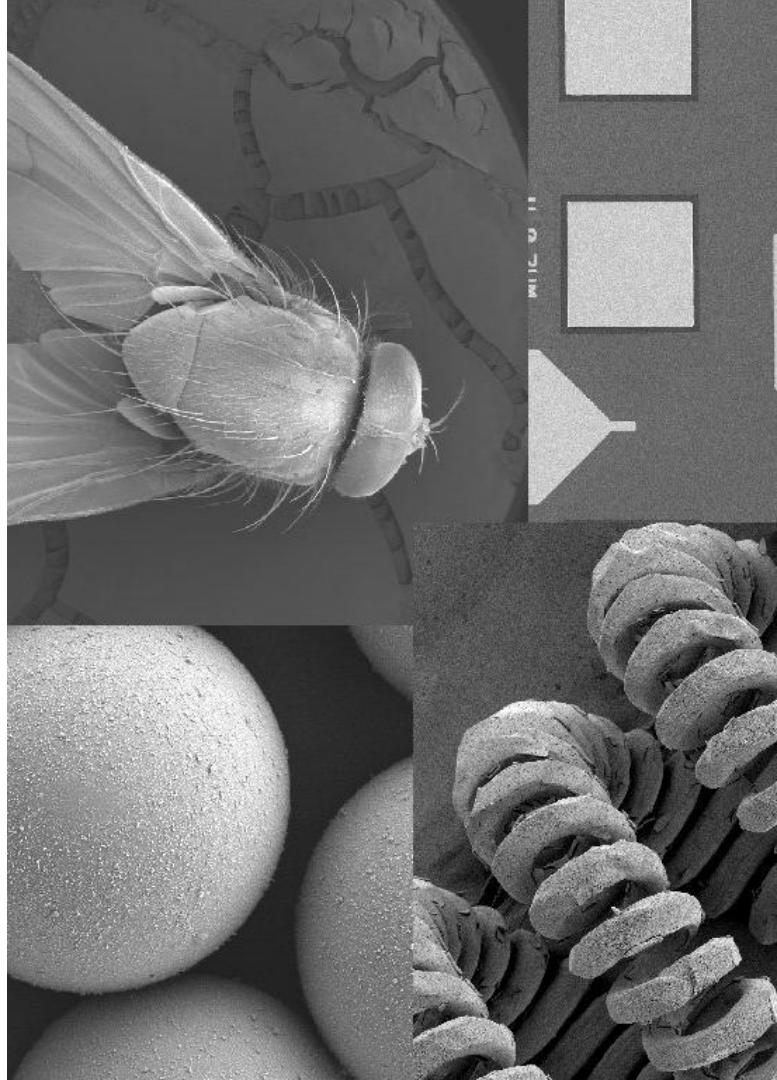


Essentials of SEM, EDX and FIB/SEM



Lucie Navratilova
Interdisciplinary Centre
for Electron Microscopy
(CIME)





SEM

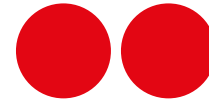
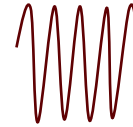
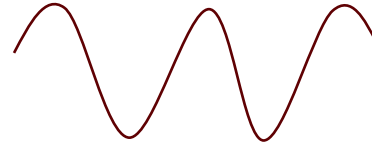
What is a SEM?

- SEM = Scanning Electron Microscope
- Focused beam of electrons to scan a sample's surface
- Magnified images of objects and features that are not visible with light microscopes



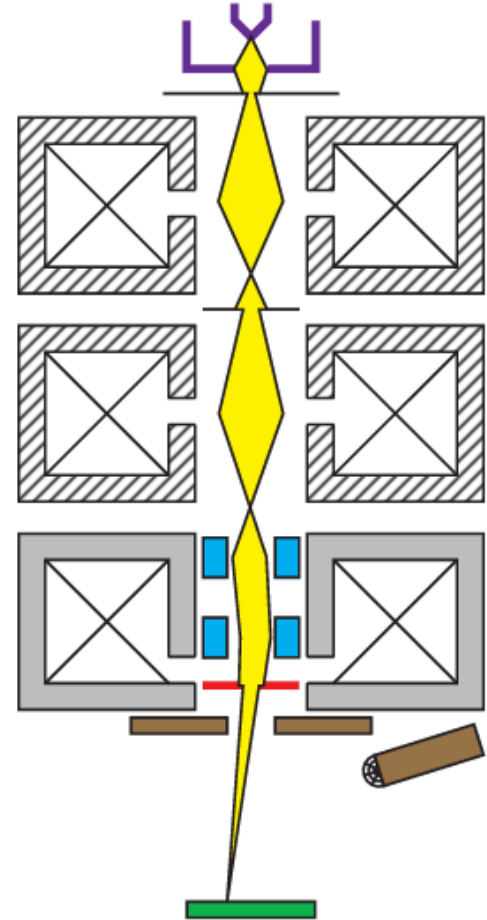
Electrons vs. light

- Resolution: the ability to distinguish between two closely spaced objects as separate entities
- Light microscopes: resolution limited by the wavelength of visible light $\sim 200\text{nm}$
- Electrons have wave/particle duality
- Electron microscopes:
 - resolution below 1nm for TEM (transmission electron microscope)
 - SEM resolution $\sim 1\text{nm}$ possible (30kV)



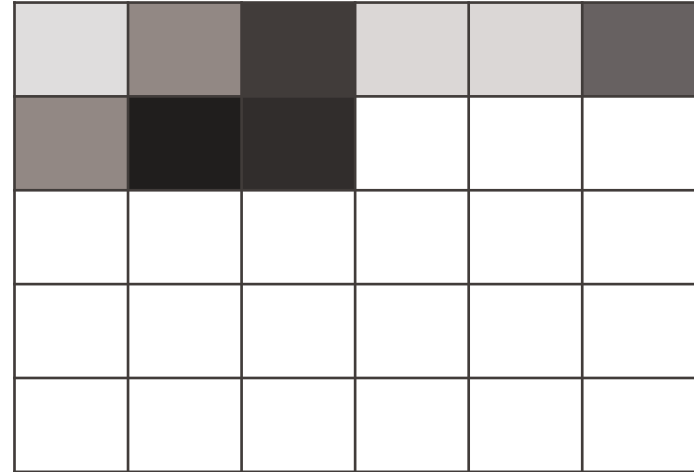
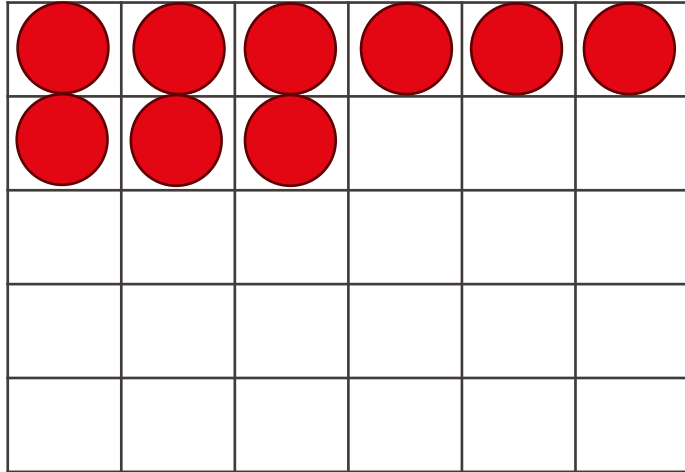
How SEM works?

- Source of electrons
- System of lenses (condenser and objective), apertures and scan coils
- Beam interactions with the sample surface
- Detectors

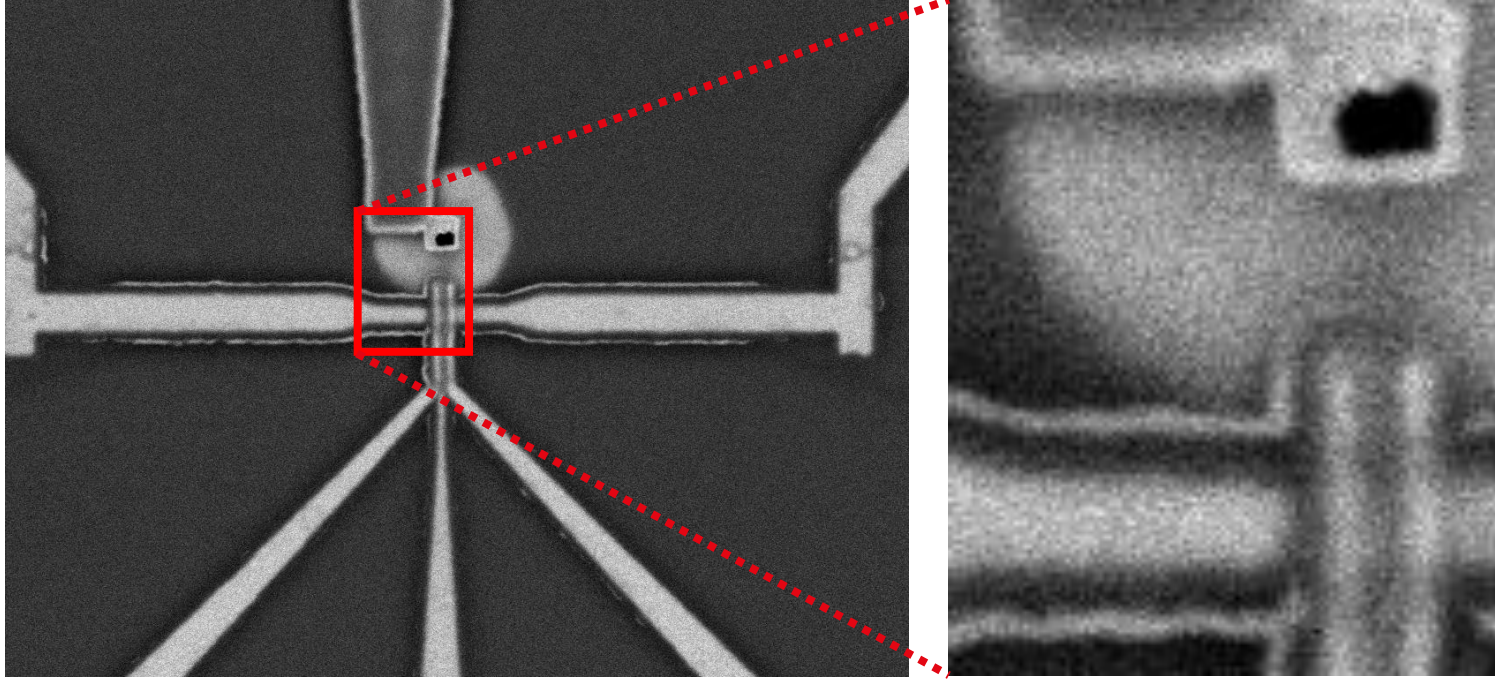


SEM image generation

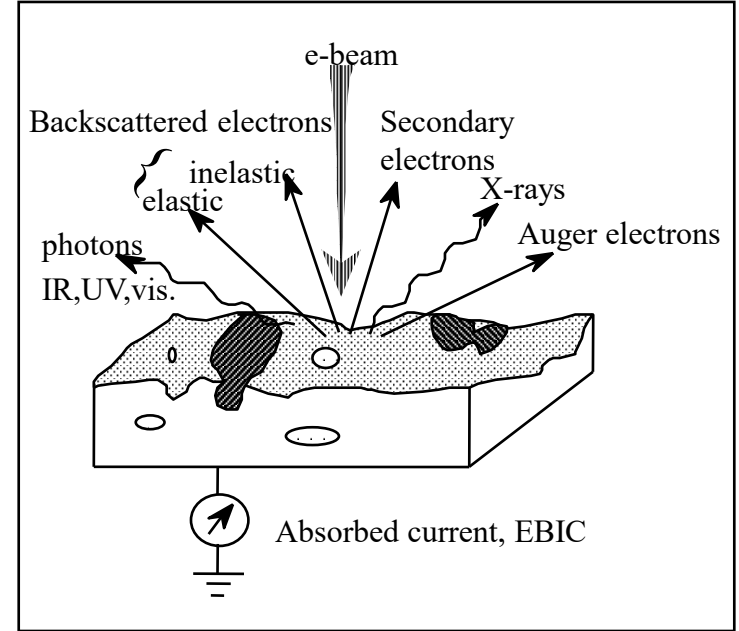
- Intensity of each pixel is proportional to signal received

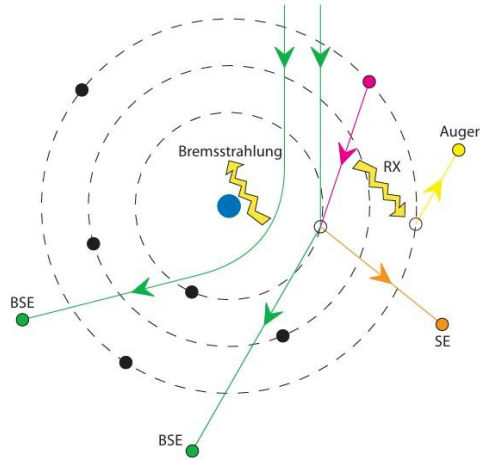


SEM image generation

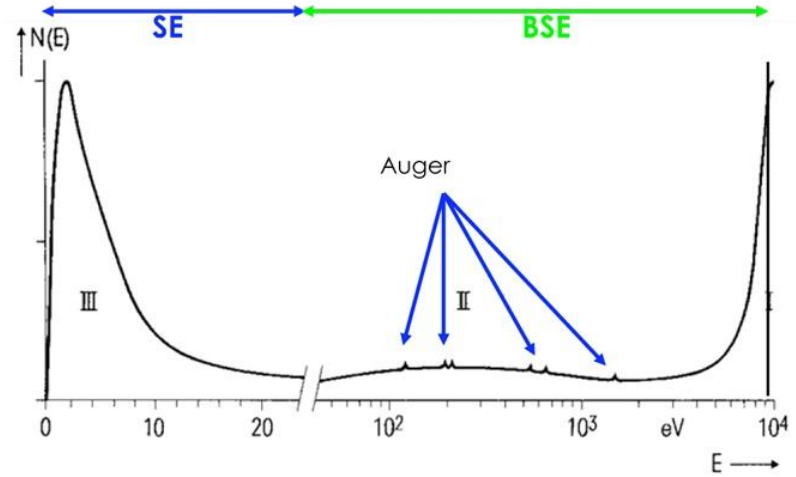


- Secondary electrons (SE)
- Backscattered electrons (BSE)
- Auger electrons
- Photons: visible, UV, IR, X-Rays
- Phonons, Heating,
- Absorption of incident electrons (EBIC-current)



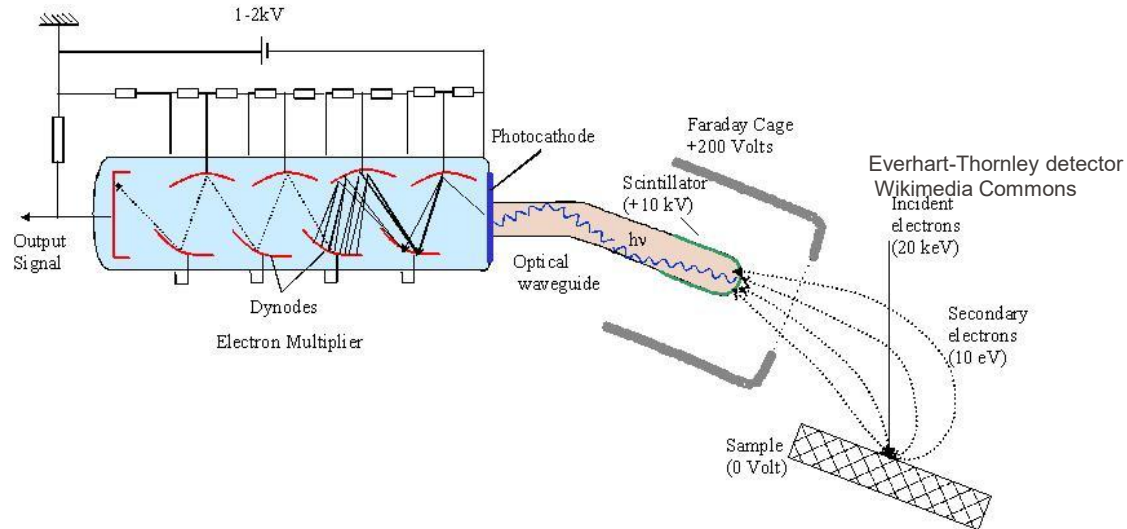


Incident electrons interactions
with an atom

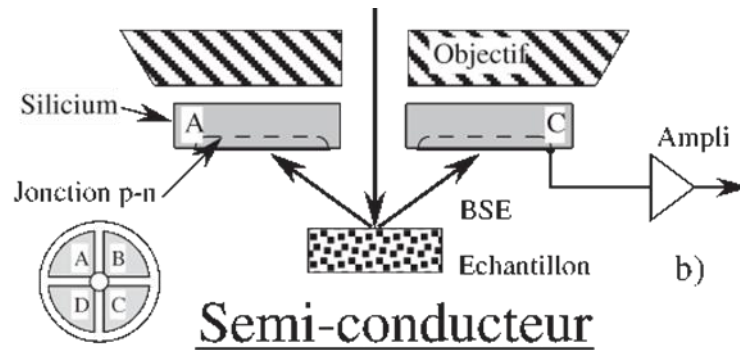


Energy spectrum of electrons
leaving a sample

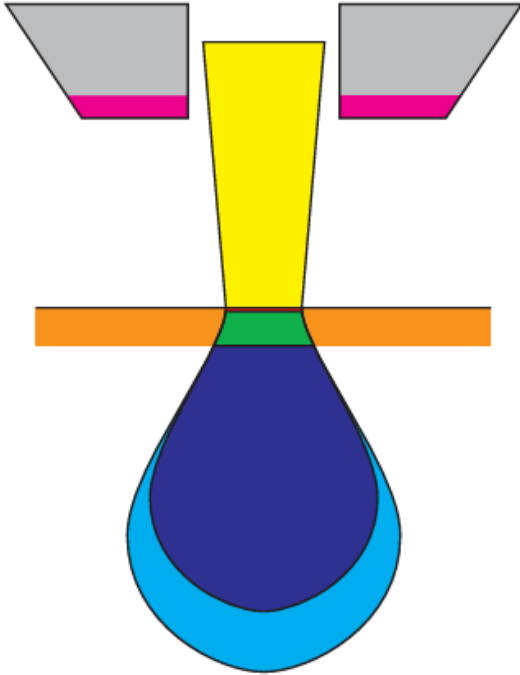
- Scintillator / Photomultiplier
- Everhart-Thornley detector (ETD)



- **Semiconductor detectors**
- Si diode with a p-n junction
- Electron-hole pairs
- Large collection angle
- Some diodes are split in 2 or 4 quadrants
- Slow (not responsive to rapid changes in signal intensity)

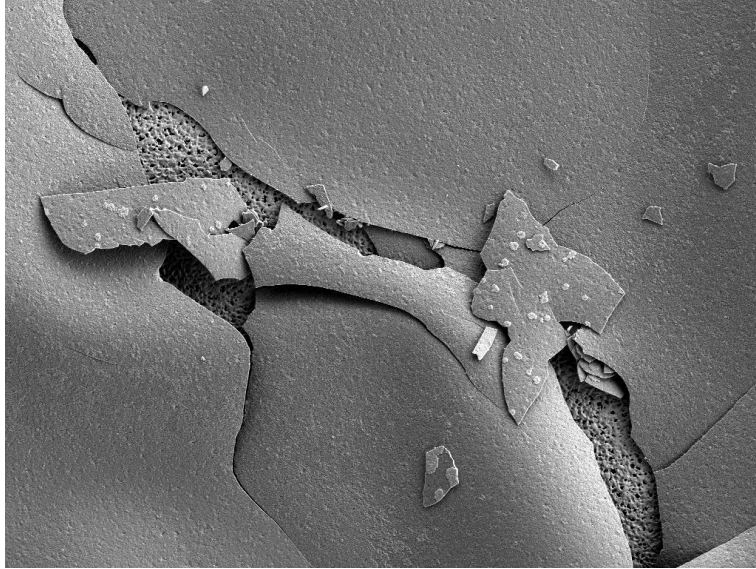


SEM interaction volume

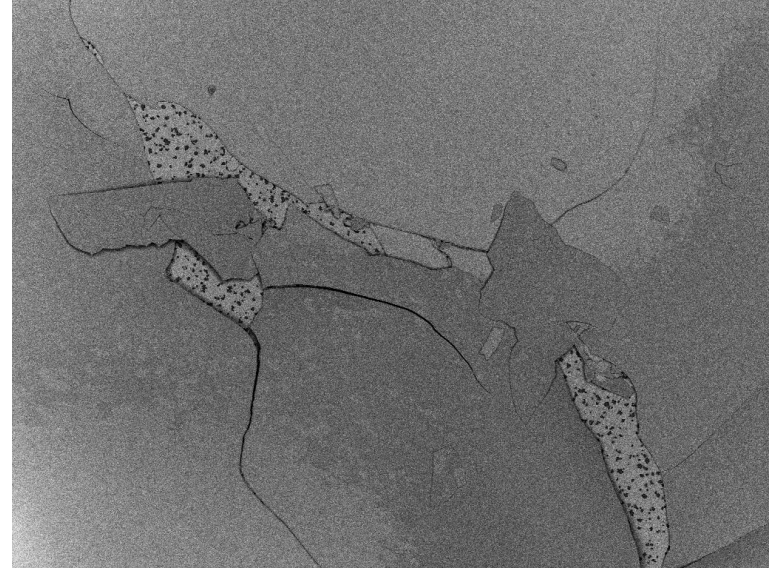


- Incident beam
- Auger electrons
- Secondary electrons (SE1)
- Backscattered electrons (BSE)
- X-Rays
- Secondary electrons (SE2)
- Secondary electrons (SE3)

SE vs. BSE image

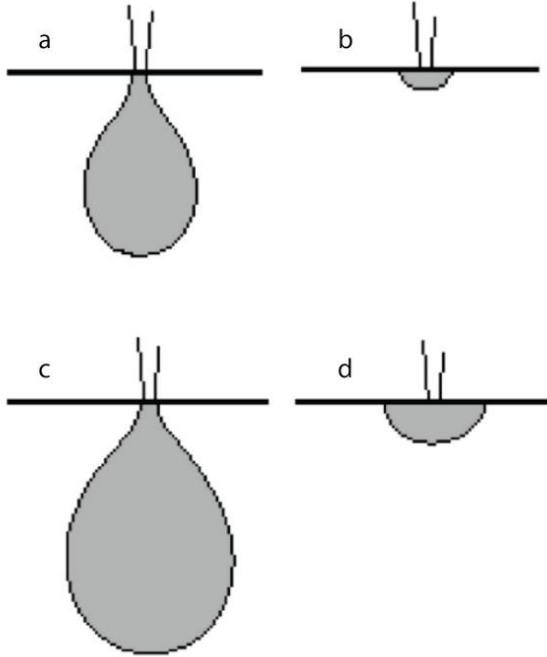


SE => topography



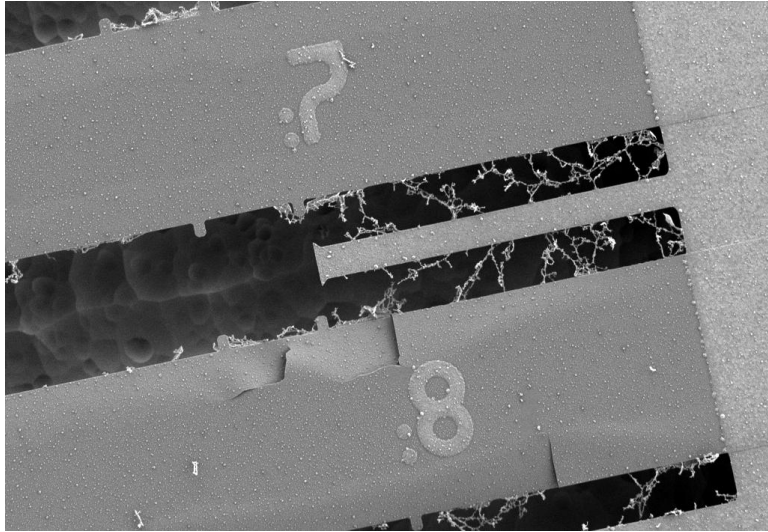
BSE => mass density contrast

SEM interaction volume

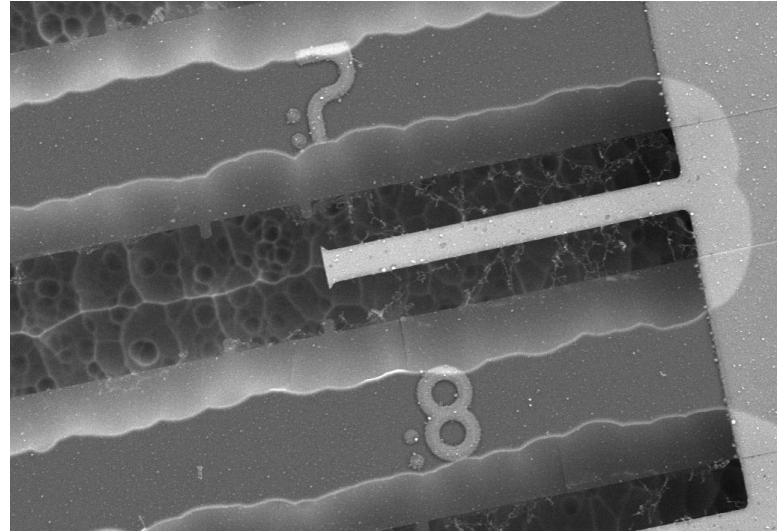


- Low Z vs. high Z
- Low vs. high acceleration voltage

SEM interaction volume



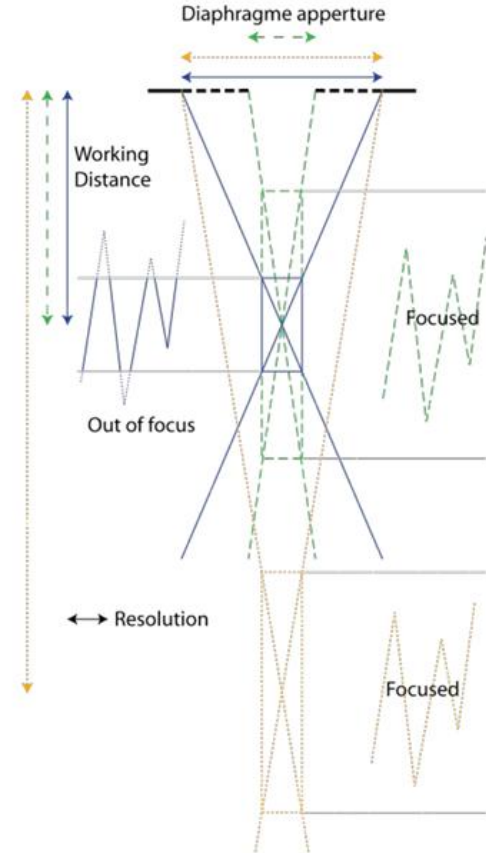
2 kV



10 kV

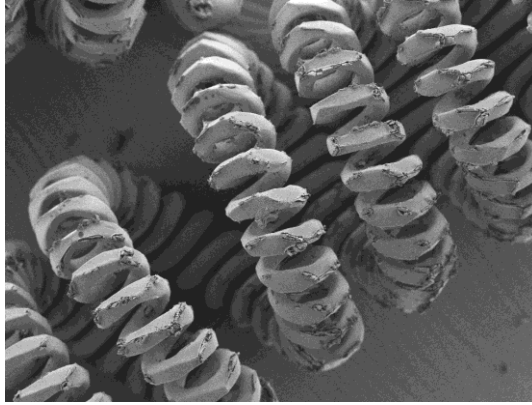
Depth of field

- The range of distances where an image appears acceptably sharp
- Probe convergence angle
 - Aperture size
 - Working distance

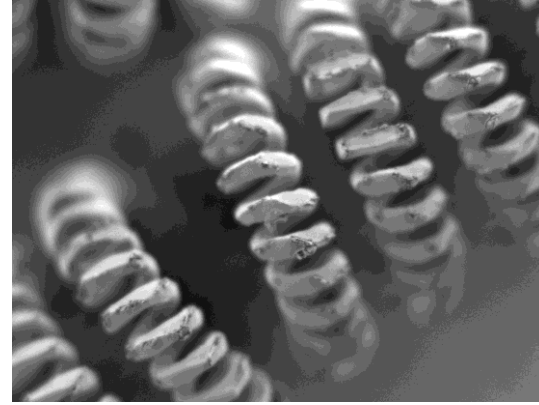


Depth of field

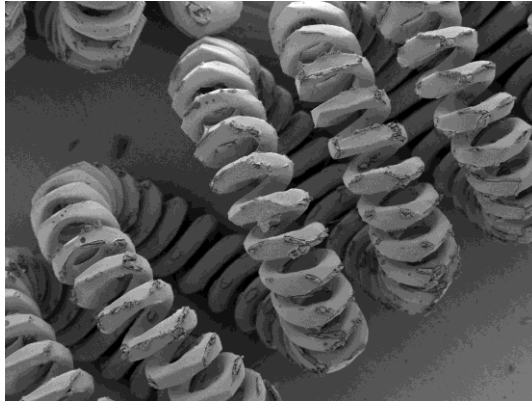
WD 5mm
Aperture size
30um

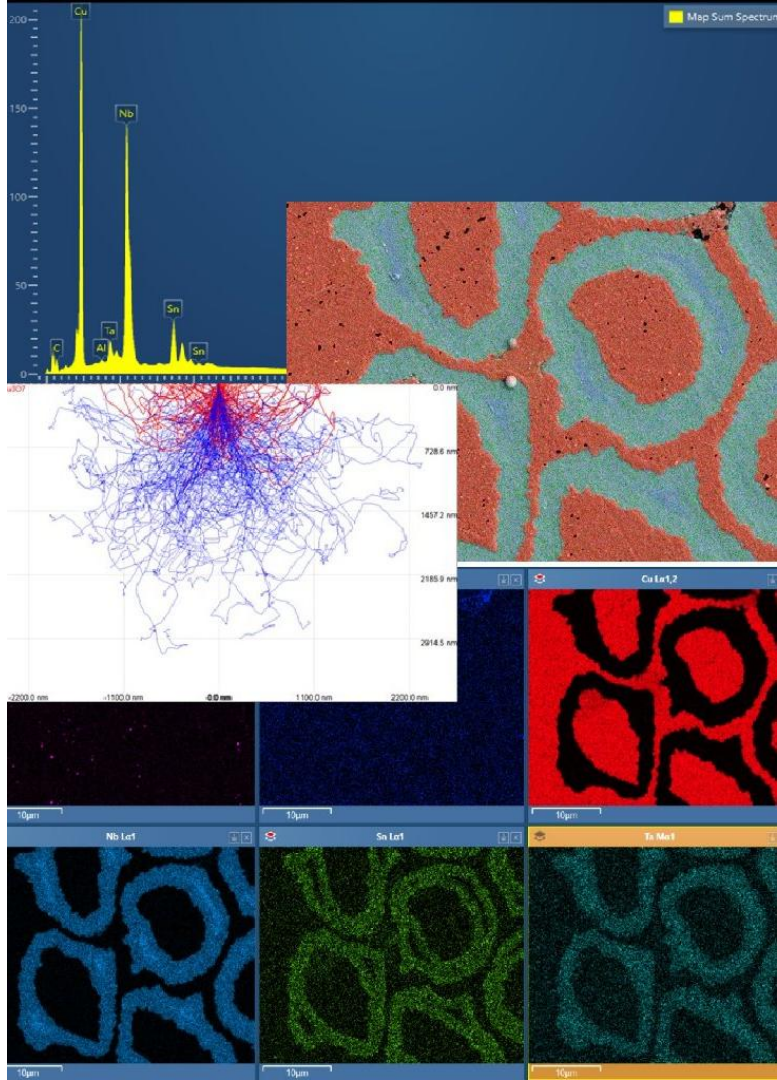


WD 5mm
Aperture size
120um



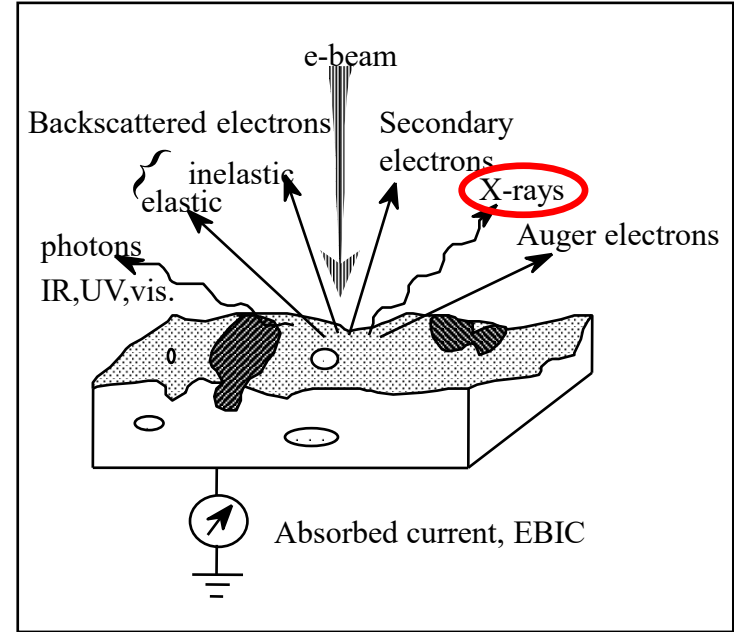
WD 15mm
Aperture size
30um



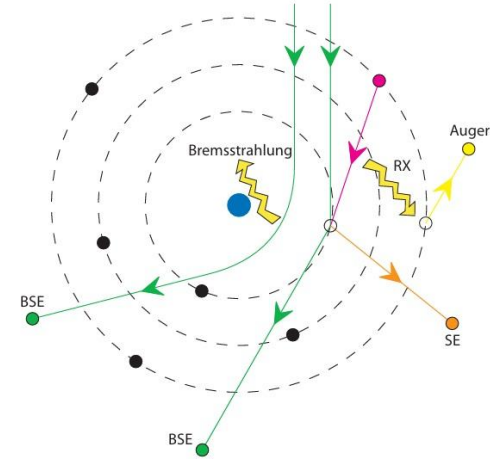


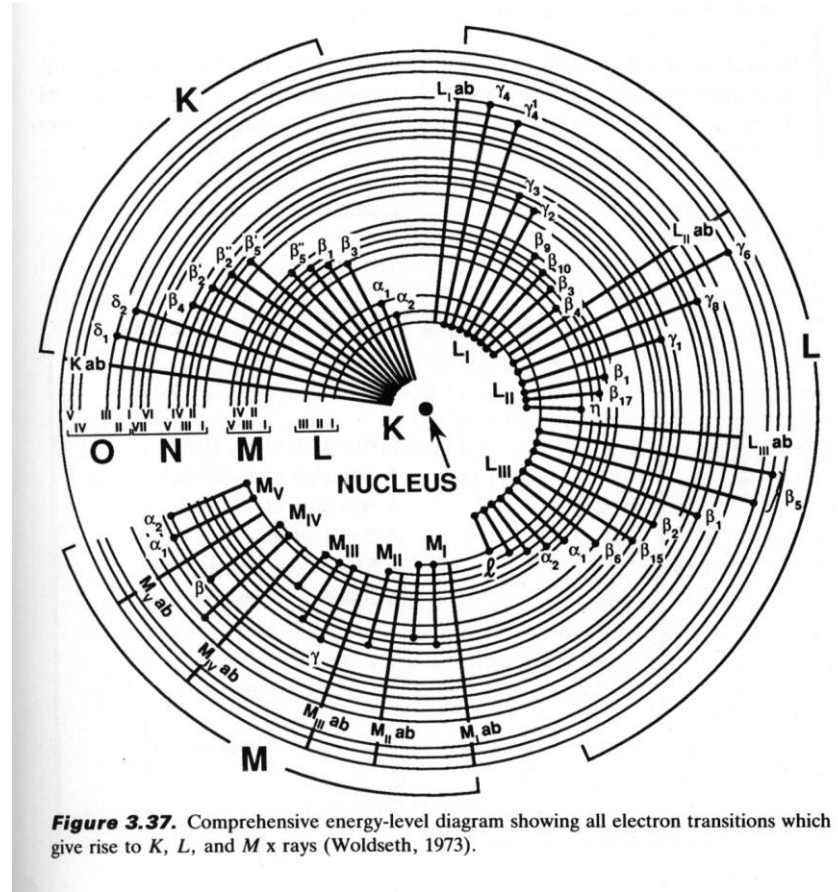
EDX

- Energy Dispersive X-ray Microanalysis
- Energy Dispersive Spectroscopy (EDS)
- Energy Dispersive X-ray spectroscopy (EDXS)
- Elemental analysis or chemical characterization technique in electron microscopes (SEM and TEM)




- Inelastic scattering of electrons at atoms
 - Continuum X-Ray production (Bremsstrahlung, Synchrotron, white radiation)
 - Characteristic X-Ray emission





AZtecLIVE powered by Ultim[®] Max

From the static to dynamic: Real-time navigation by chemistry



The image shows the AZtecLIVE XRF spectrometer, a handheld device used for elemental analysis. It is positioned in the center of the slide, with a callout box highlighting its key features.

Key

Symbol: **Ru** 44

Atomic number: 44

Principal lines keV: **101.07**

Atomic weight: **101.07**

Kα: **19.2365**

Lα: **2.5586**

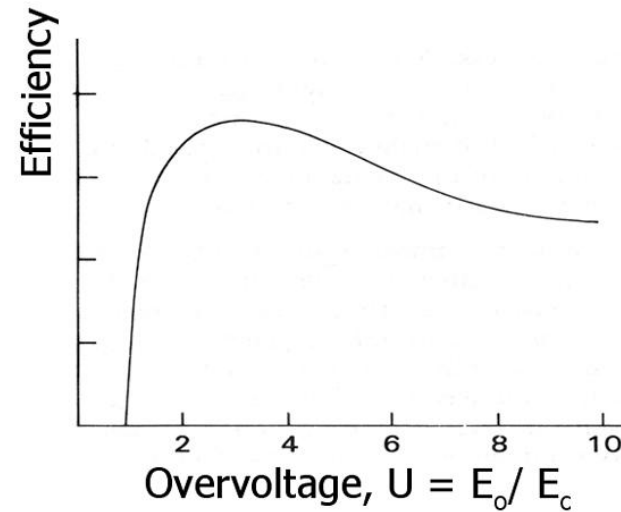
Density ρ g/cm³: **12.20**

| | | | | | | | | | | | | | | | | | |
|----------------------|-----------------------|-----------------------|-----------------------|--------------------------|------------------------|------------------------|-----------------------|-----------------------|------------------------|-----------------------|-------------------------|-------------------------|-----------------------|--------------------------|-----------------------|-------------------------|---------------------|
| 1 | | | | | | | | | | | | | | | | | 18 |
| H 1 Hydrogen | | | | | | | | | | | | | | | | | He 2 Helium |
| Li 3 Lithium | Be 4 Beryllium | | | | | | | | | | | B 5 Boron | C 6 Carbon | N 7 Nitrogen | O 8 Oxygen | F 9 Fluorine | Ne 10 Neon |
| Na 11 Sodium | Mg 12 Magnesium | | | | | | | | | | | Al 13 Aluminum | Si 14 Silicon | P 15 Phosphorus | S 16 Sulfur | Cl 17 Chlorine | Ar 18 Argon |
| K 19 Potassium | Ca 20 Calcium | Sc 21 Scandium | Ti 22 Titanium | V 23 Vanadium | Cr 24 Chromium | Mn 25 Manganese | Fe 26 Iron | Co 27 Cobalt | Ni 28 Nickel | Cu 29 Copper | Zn 30 Zinc | Ga 31 Gallium | Ge 32 Germanium | As 33 Arsenic | Se 34 Selenium | Br 35 Bromine | Kr 36 Krypton |
| Rb 37 Rubidium | Sr 38 Strontium | Y 39 Yttrium | Zr 40 Zirconium | Nb 41 Niobium | Mo 42 Molybdenum | Tc 43 Technetium | Ru 44 Ruthenium | Rh 45 Rhodium | Pd 46 Palladium | Ag 47 Silver | Cd 48 Cadmium | In 49 Indium | Sn 50 Tin | Sb 51 Antimony | Te 52 Tellurium | I 53 Iodine | Xe 54 Xenon |
| Cs 55 Cesium | Ba 56 Barium | La 57 Lanthanum | Hf 72 Hafnium | Ta 73 Tantalum | W 74 Tungsten | Re 75 Rhenium | Os 76 Osmium | Ir 77 Iridium | Pt 78 Platinum | Au 79 Gold | Hg 80 Mercury | Tl 81 Thallium | Pb 82 Lead | Bi 83 Bismuth | Po 84 Polonium | At 85 Astatine | Rn 86 Radon |
| Fr 87 Francium | Ra 88 Radium | Ac 89 Actinium | | | | | | | | | | | | | | | |
| | | | Ce 58 Cerium | Pr 59 Praseodymium | Nd 60 Neodymium | Pm 61 Promethium | Sm 62 Samarium | Eu 63 Europium | Gd 64 Gadolinium | Tb 65 Terbium | Dy 66 Dysprosium | Ho 67 Holmium | Er 68 Erbium | Tm 69 Thulium | Yb 70 Ytterbium | Lu 71 Lutetium | |
| | | | Th 90 Thorium | Pa 91 Protactinium | U 92 Uranium | Np 93 Neptunium | Pu 94 Plutonium | Am 95 Americium | Cm 96 Curium | Bk 97 Berkelium | Cf 98 Californium | Es 99 Einsteinium | Fm 100 Fermium | Md 101 Mendelevium | No 102 Nobelium | Lr 103 Lawrencium | |



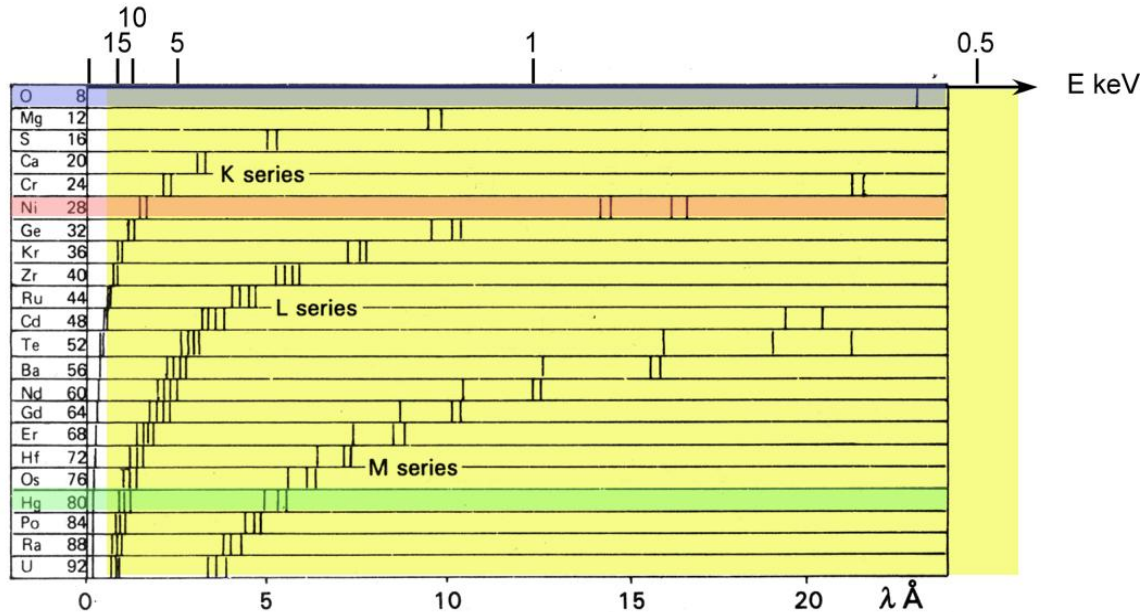
X-Rays generation efficiency

- Overvoltage $U = E_0 / E_{\text{ionization}}$



Characteristic lines: Moseley's Law

There is a relationship between the energy of the Characteristic X-ray lines for each element and its atomic number: the energy is proportional to the square of the atomic number, Z .

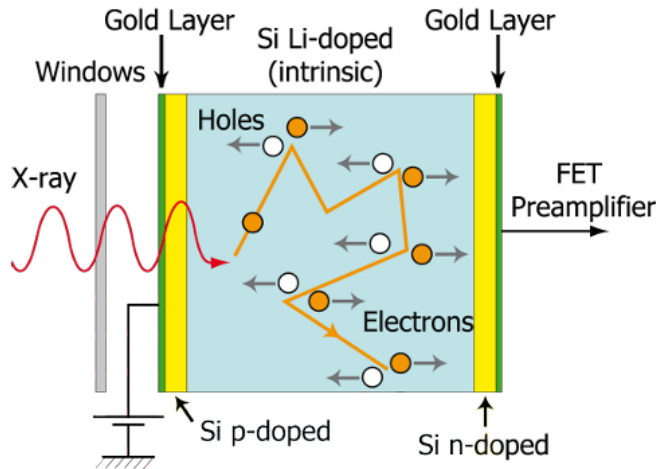


Known ambiguities:

Al K α = Br L I

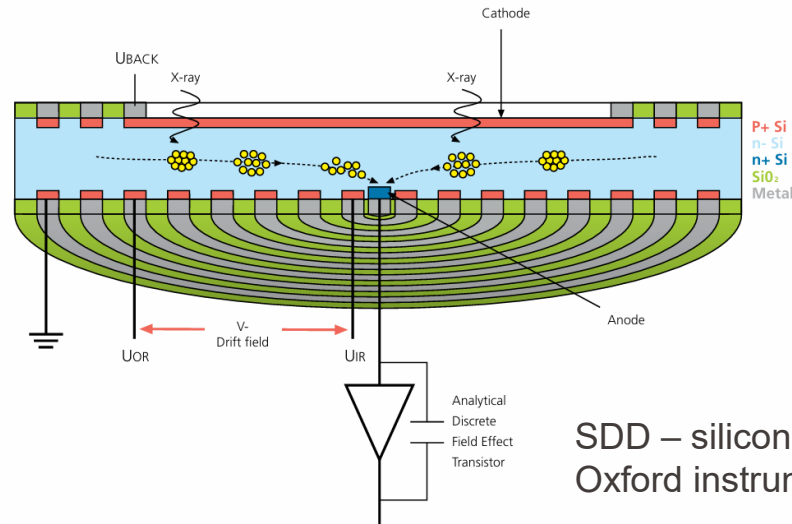
S K α = Mo L I

How EDX detector works



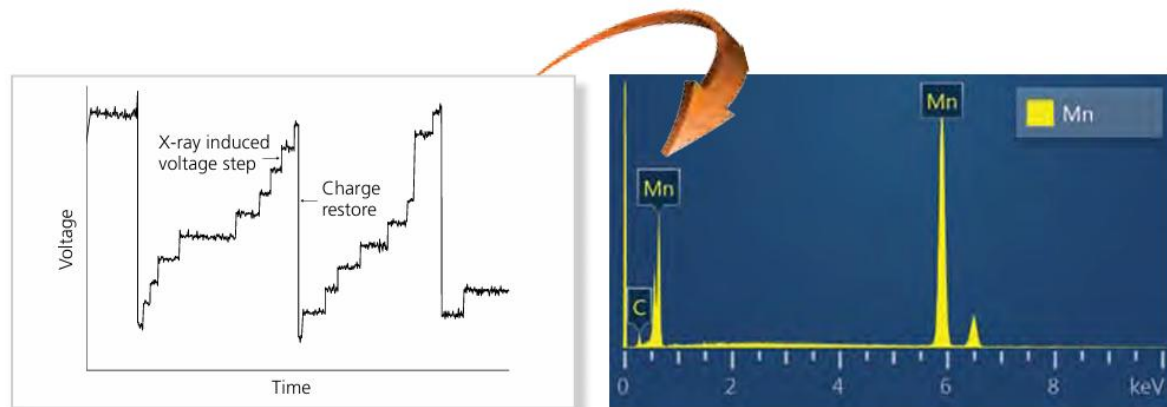
- Li-doped Si single crystal semiconductor
- X-Ray is converted into a charge by the ionization of atoms in the semiconductor crystal
- Electron-hole pairs – number proportional to the energy of the X-Ray
- Electrons collected to the anode
- X-Ray energies are measured as electric voltage pulses
- Cooling by liquid nitrogen – to prevent Li diffusion and to reduce a dark current (thermal noise)

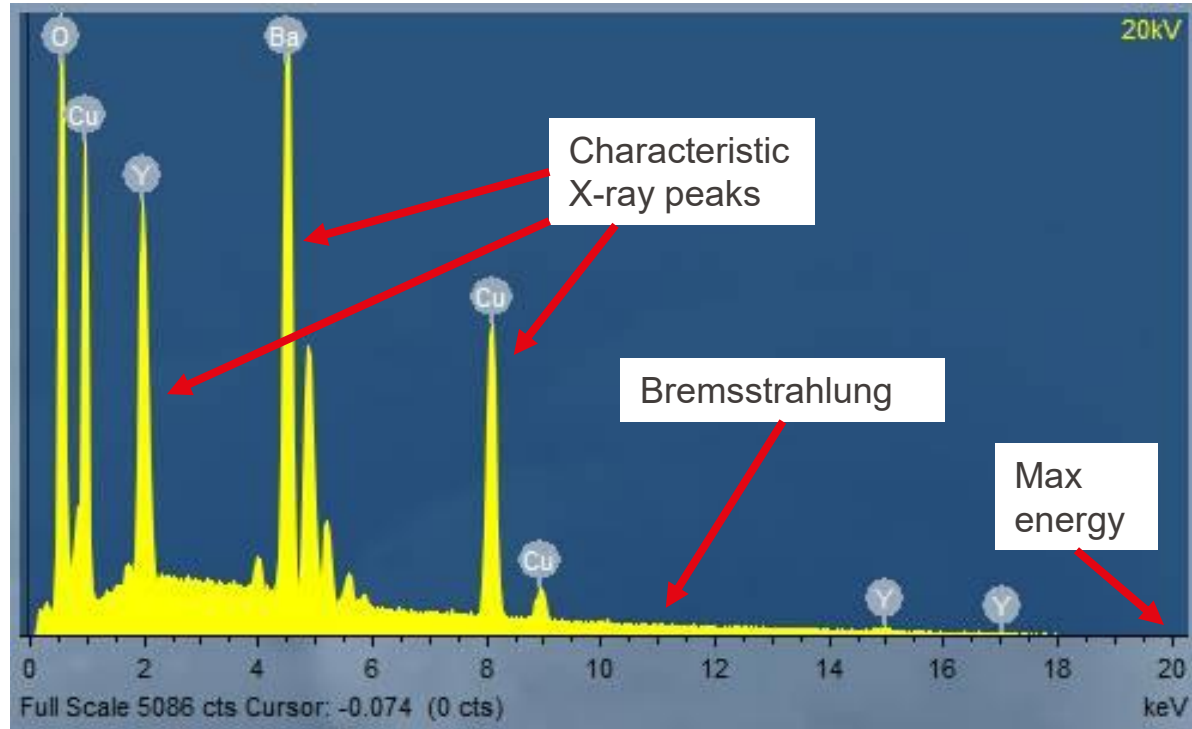
- SDD sensor – high purity silicon with a large area contact
- Central small anode contact, surrounded by a number of concentric drift electrodes
- X-Ray is converted into an electron cloud
- Electrons drifted down a field gradient applied between the drift rings
- Peltier cooling



SDD – silicon drift detector
Oxford instruments

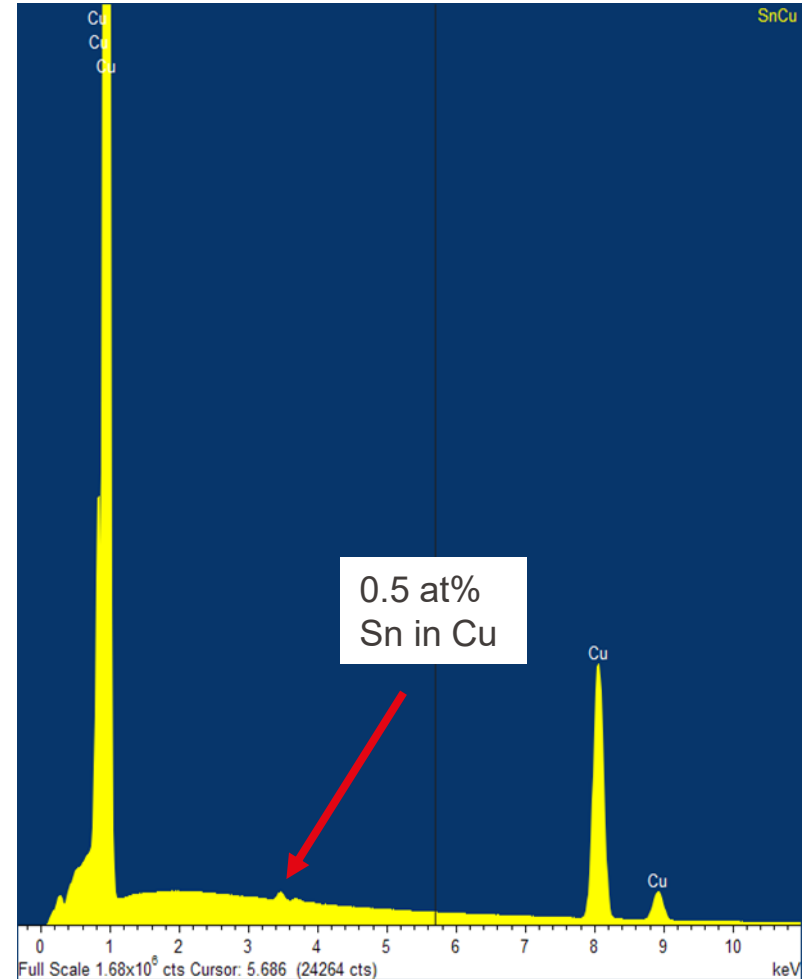
- The charge is converted into the voltage signal by the FET preamplifier
- The output from the preamplifier is a voltage “ramp” – X-ray charge + leakage current
- The voltage signal is input into the pulse processor for measurement



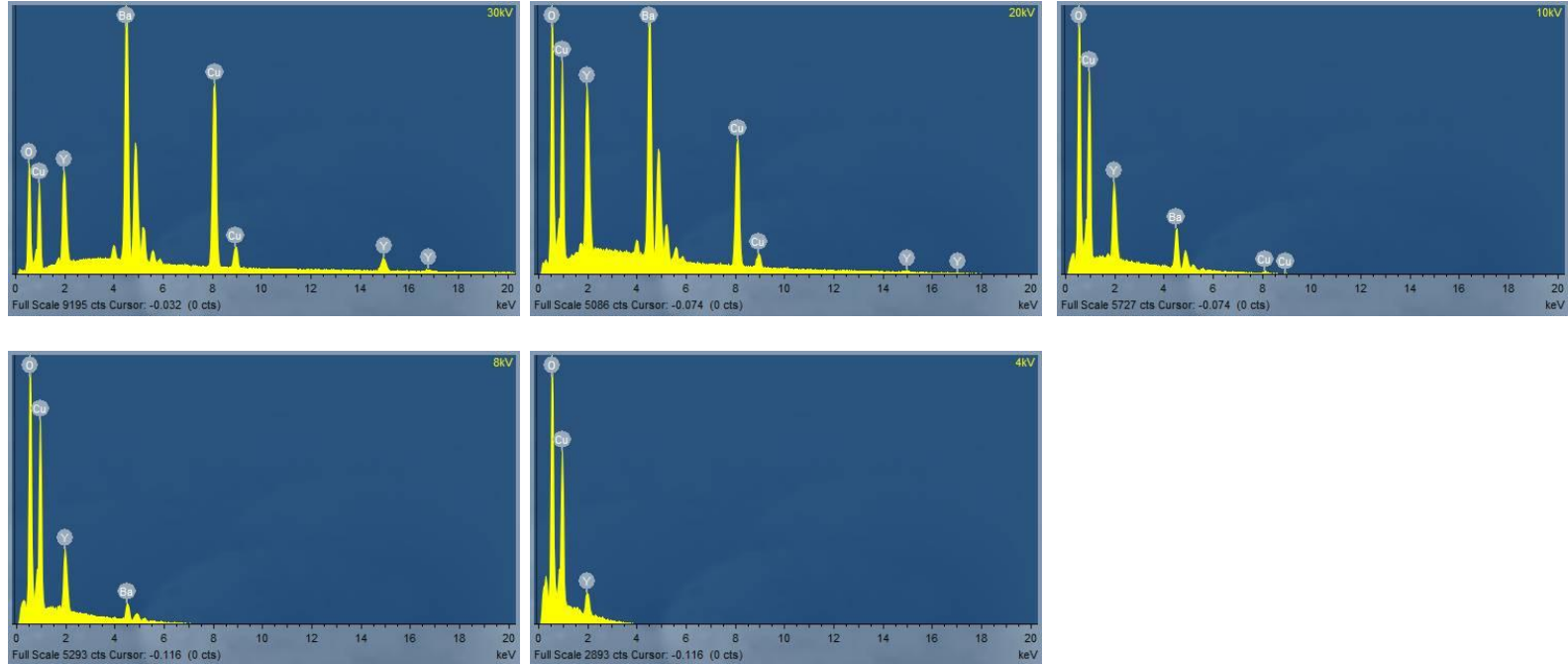


Spectrum simulation $\text{YBa}_2\text{Cu}_3\text{O}_7$ at 20kV

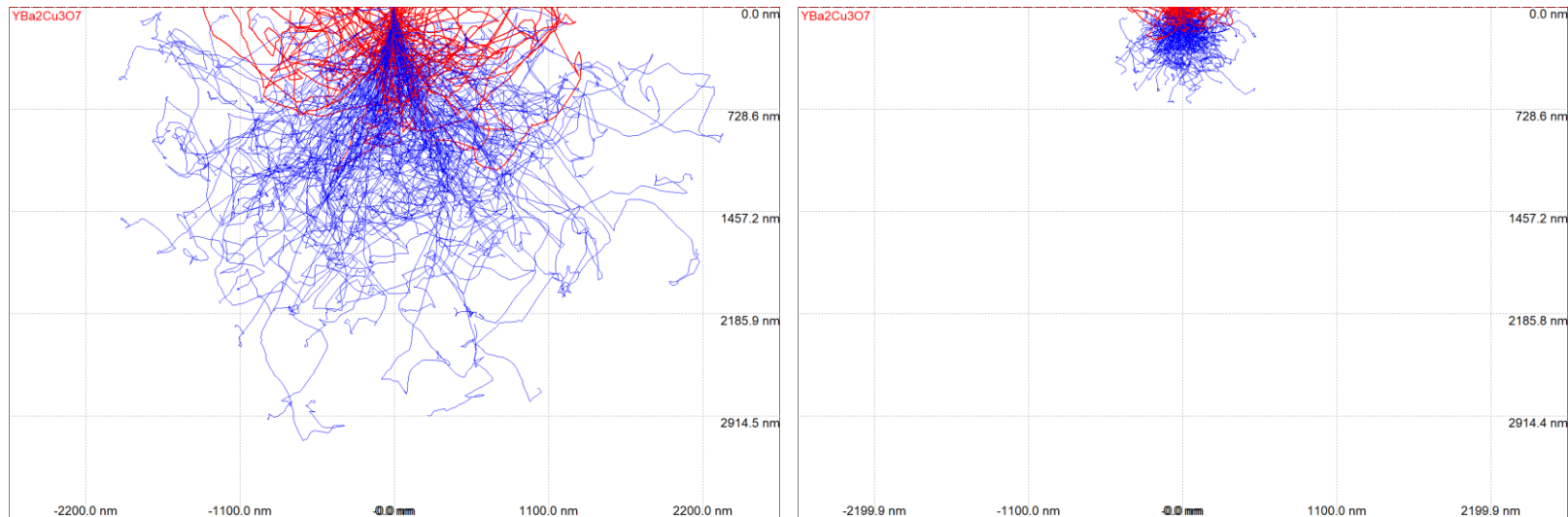
- Acquisition under best conditions
=> detection of $\sim 0,5$ at% for almost all elements for acquisition times of 100sec



Choice of HV in SEM



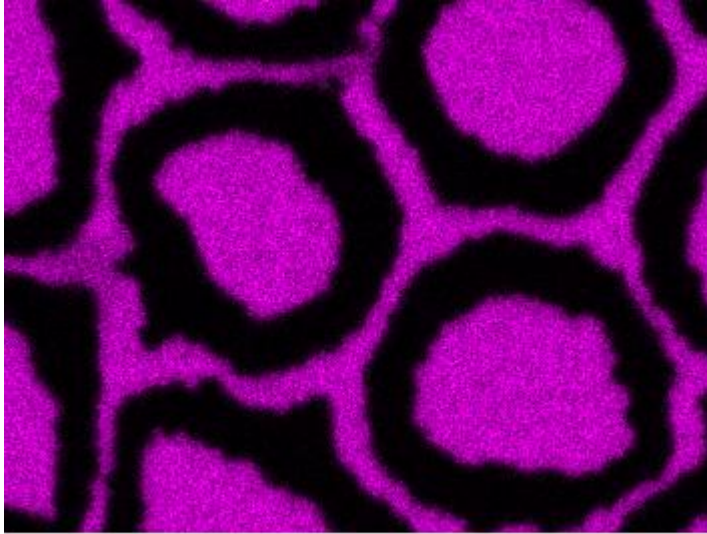
Sample: $\text{YBa}_2\text{Cu}_3\text{O}_7$



Monte-Carlo Simulation of electron trajectories with CASINO

20kV vs. 8kV resolution

Cu-L

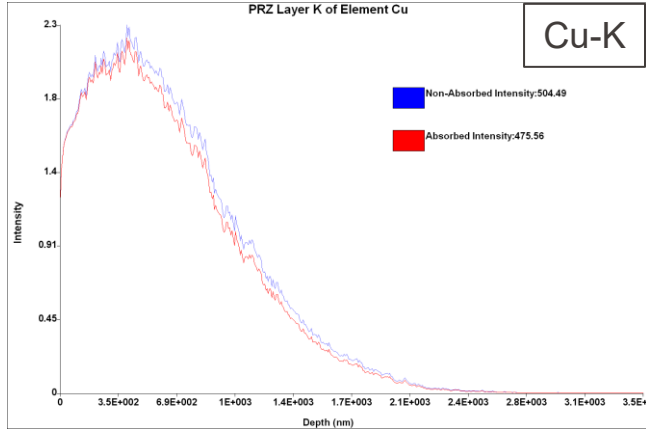


Cu-L

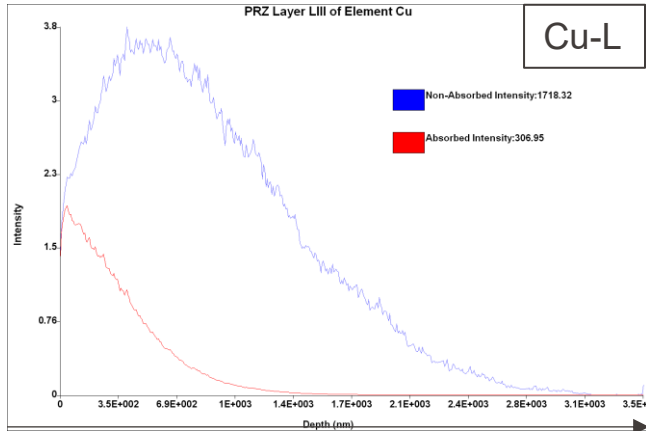


20kV vs. 8kV – absorption issue

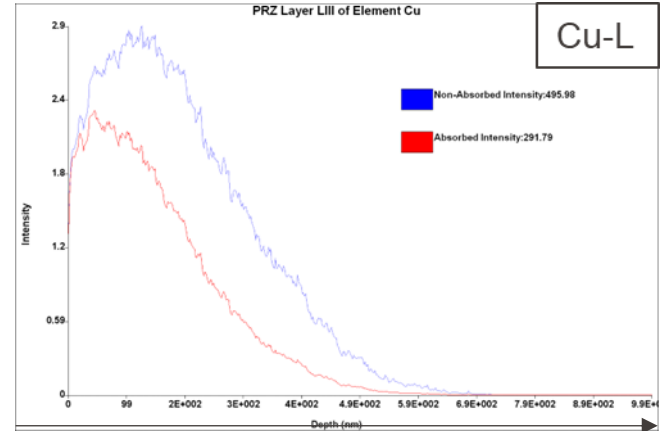
20kV



X-rays generated
X-rays detected

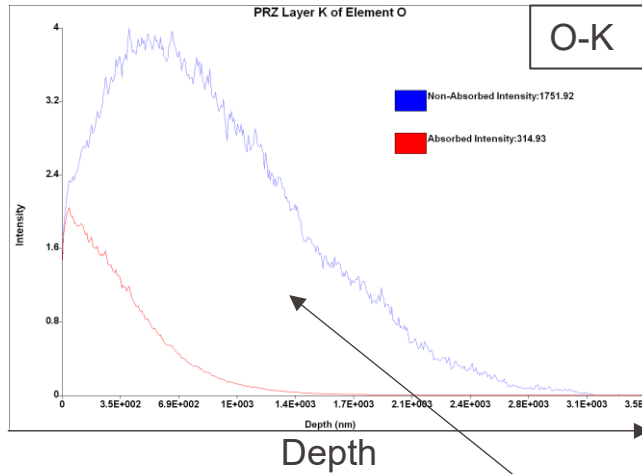


8kV

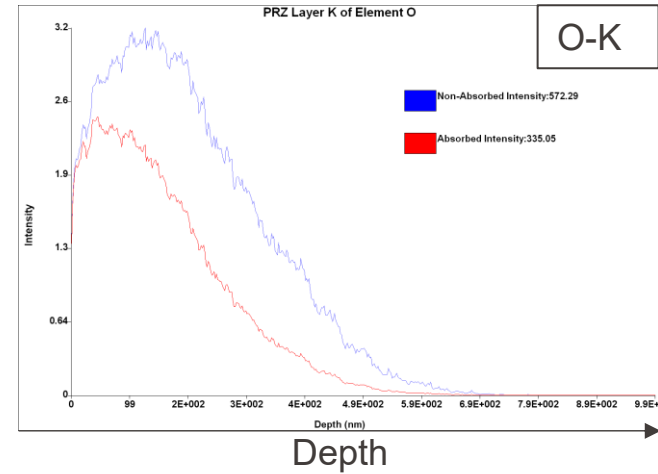


20kV vs. 8kV – absorption issue

20kV



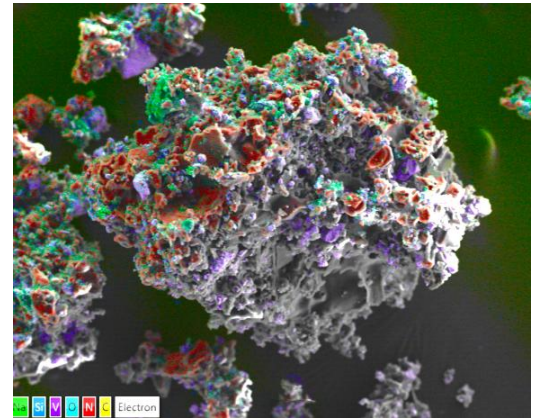
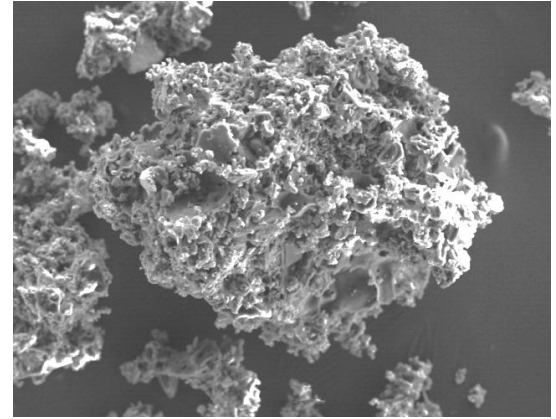
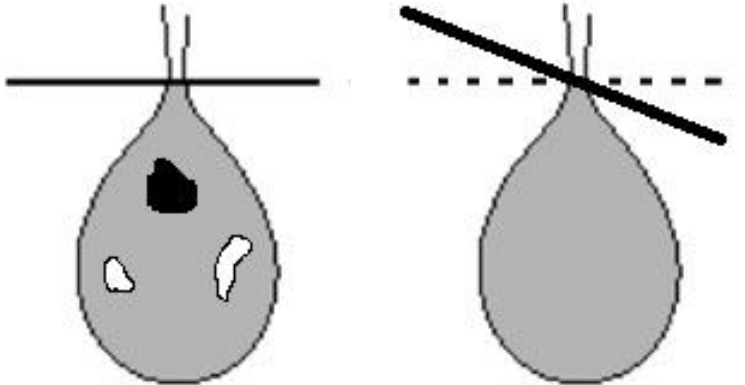
8kV



Not detected by detector
due to absorption

Ideal sample

- Flat surface without contamination
- Horizontal orientation
- Homogeneous sample (no inclusions, voids,...)



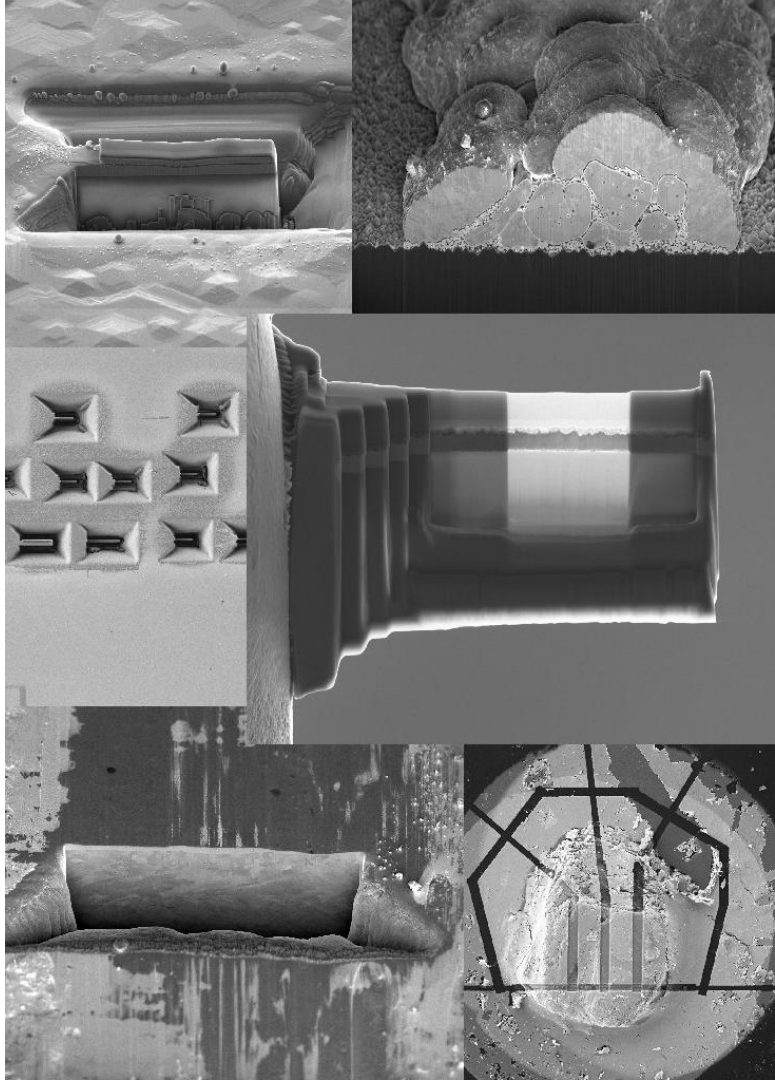
When the going gets tough...

- Acquisition under best conditions - sample, position, HV,...
- Comparison with a standard sample (known concentration, same conditions)
- Standardless – theoretical calculation, possible with high accuracy, light elements are critical

- Correction methods

$$[Z \times A \times F] \frac{C_i}{C_i^{std}} = \frac{I_i}{I_i^{std}} = k_i$$

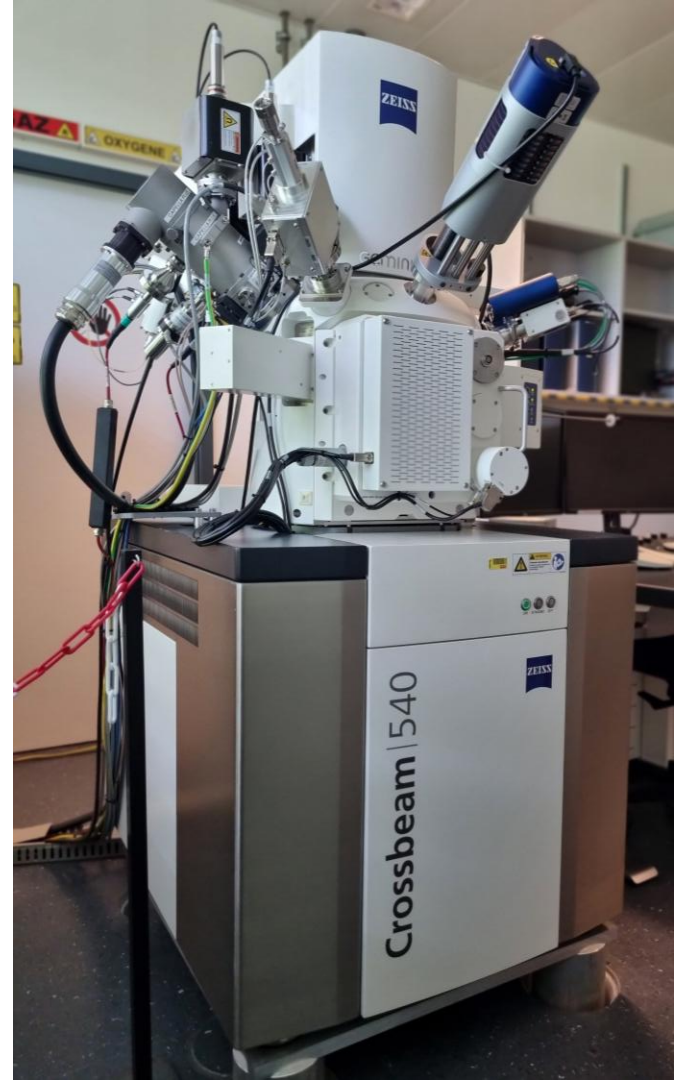
- Z – how the electron beam penetrates in the sample and loose energy (Z and density dependant)
- A – absorption of the X-rays along the path to sample surface
- F – adds some photons when (secondary) fluorescence occurs



FIB/SEM

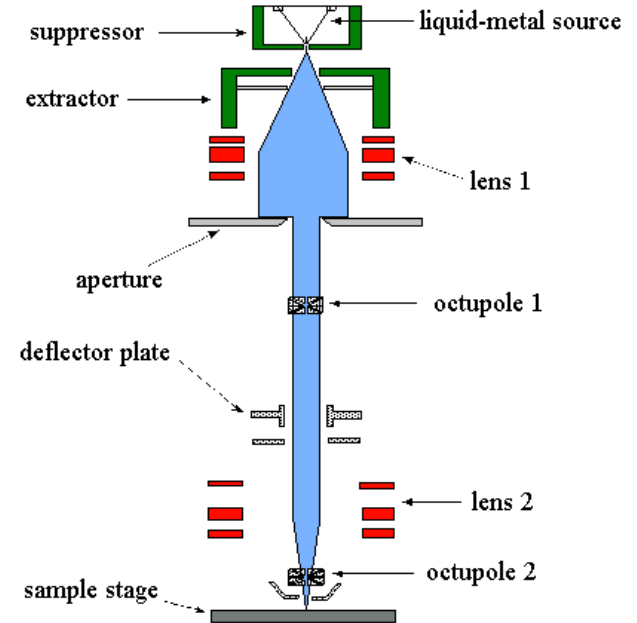
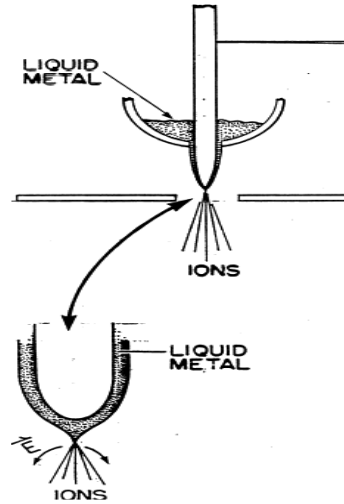
What is a FIB/SEM?

- FIB = Focused Ion Beam
- FIB/SEM = dual beam/ cross beam microscope
- SEM goes 3D



- Source: liquid metal ion source (LMIS)
- Ga, Au, Ir
- (Xe, Ar, N, O)

- Why Ga?
 - Metallic
 - Low melting point
 - In the middle of periodic table
 - No overlap for EDX



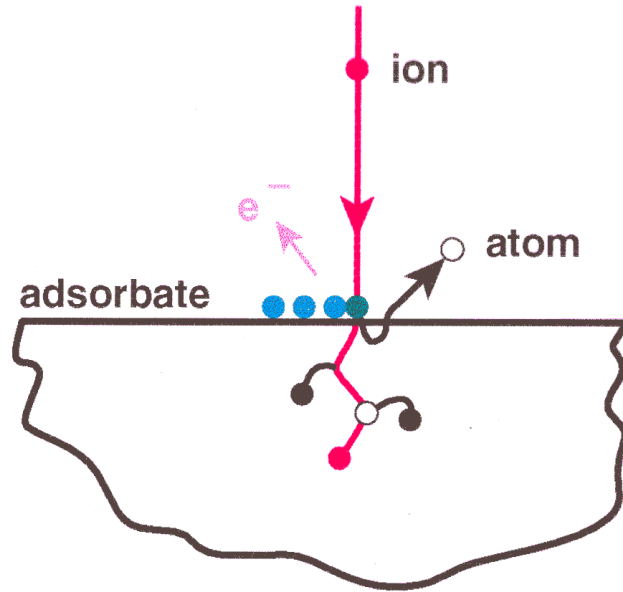
Schematic diagram of a FIB ion column
Source: IBM Almaden Research Center

▪ Electrons:

- Small
- Inner shell reactions
- High penetration depth
- Low mass – higher speed for given energy
- Negative
- Magnetic lens

▪ Ions:

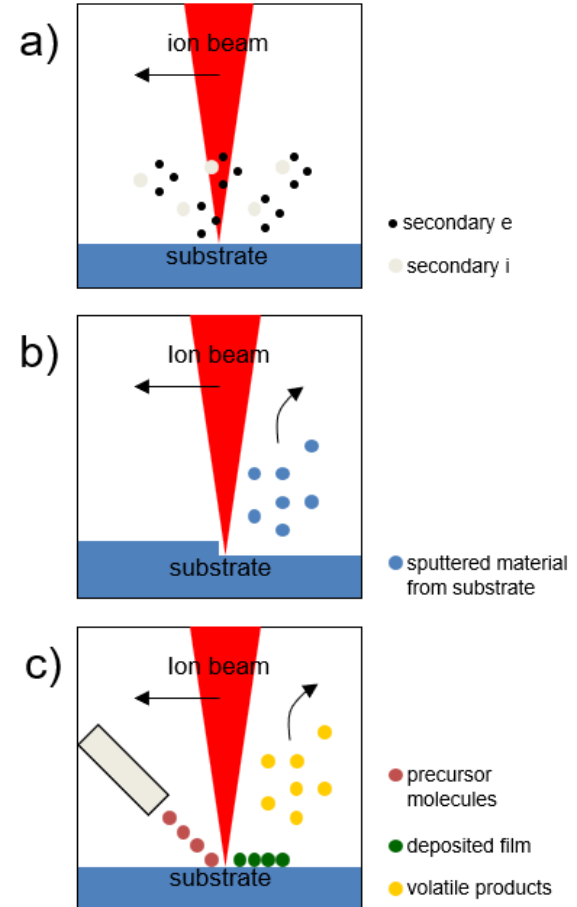
- Big
- Outer shell reactions (no X-Rays)
- High interaction probability
- Less penetration depth
- Can remain trapped – doping
- High mass – slow speed but high momentum
 - Milling
- Positive
- Electrostatic lenses



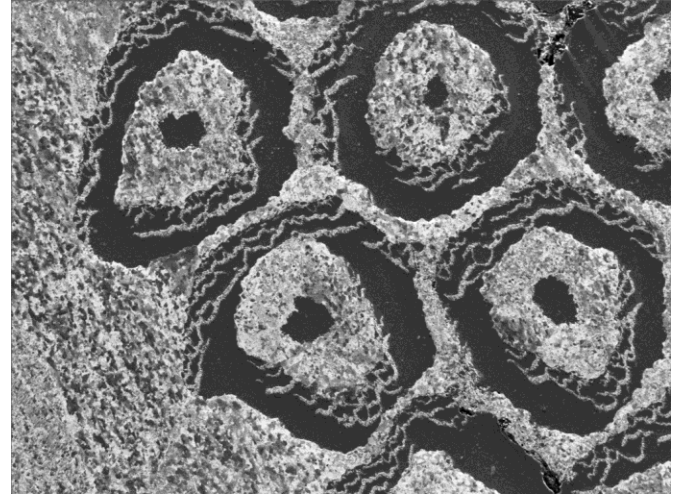
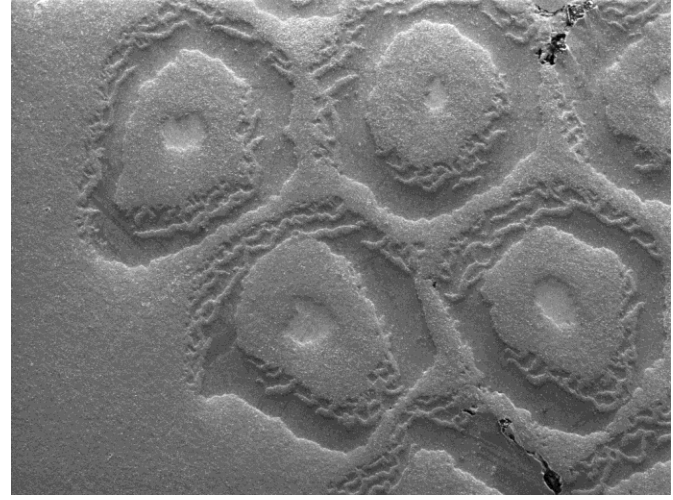
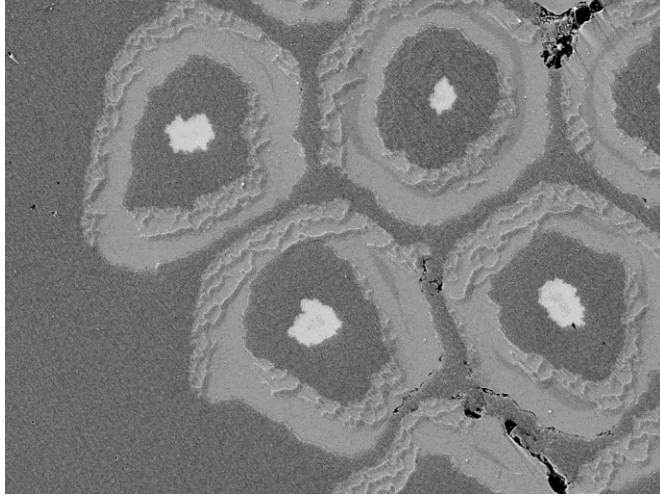
- SE emission – SE image (2-3 SE per ion)
- Sputtering
- Damage – displacement of atoms in the solid
- Ion implantation

3 basic operating modes

- FIB imaging
 - Emission of secondary electrons and ions
 - Low ion currents
- FIB milling
 - Sputtering of substrate atoms
 - High ion currents
- FIB deposition/enhanced etching
 - Gas assisted chemical interactions

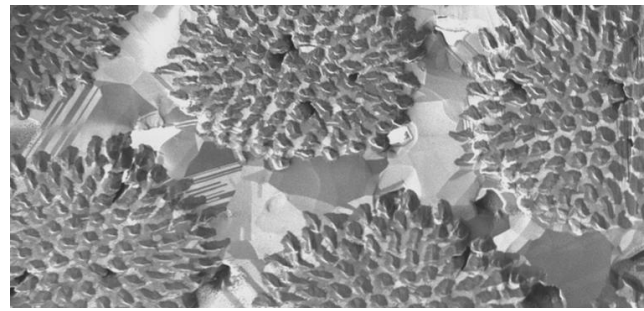


SEM image vs. FIB image

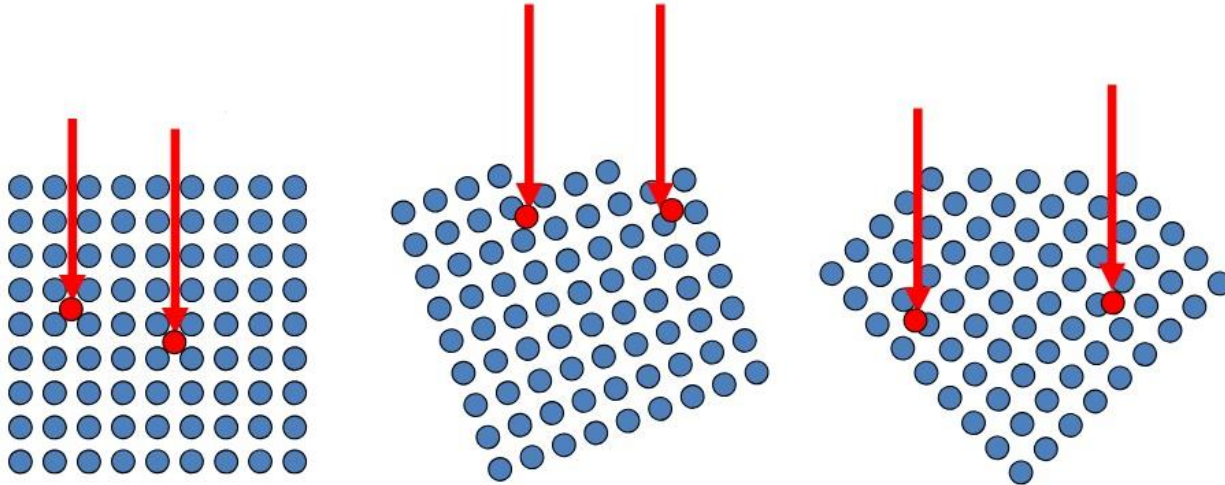


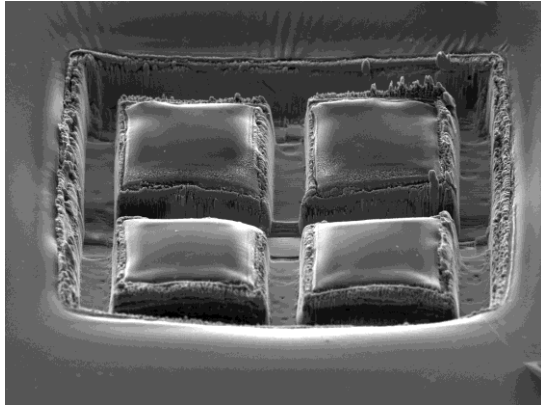
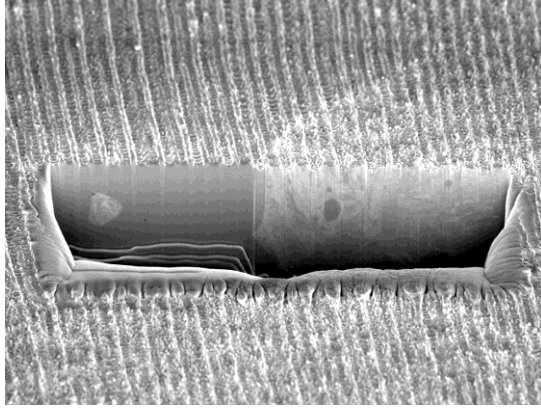
FIB imaging

Channelling contrast



- Atom columns aligned with the ion trajectory => deeper penetration => less sputtering and less SE electrons





| Material | Sputter rate ($\mu\text{m}^3/\text{nC}$) |
|--------------------------------|--|
| C | 0.18 |
| Al | 0.29-0.37 |
| Si | 0.15-0.27 |
| Ti | 0.37-0.46 |
| Fe | 0.29 |
| W | 0.11-0.12 |
| Au | 1.5-1.8 |
| SiO ₂ | 0.19-0.24 |
| TiO | 0.15 |
| Al ₃ O ₂ | 0.30 - 0.42 |

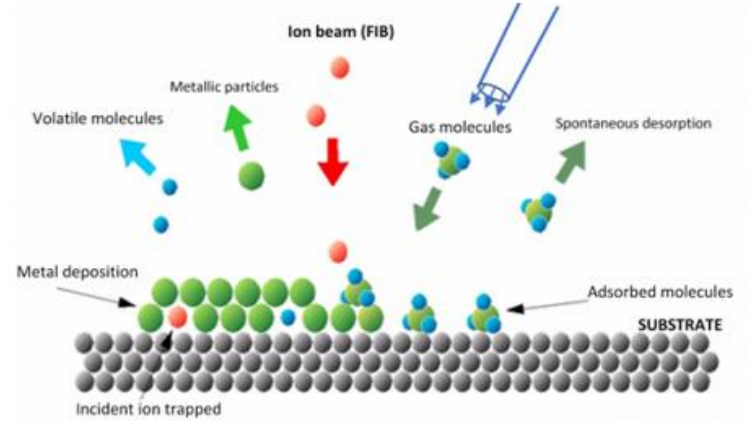
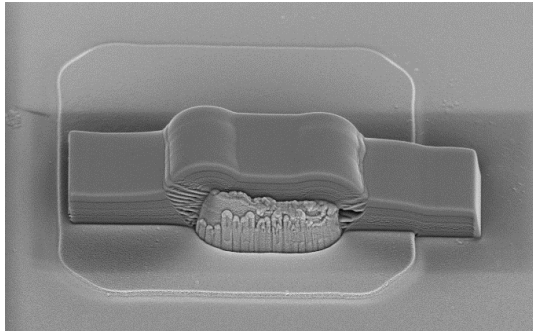
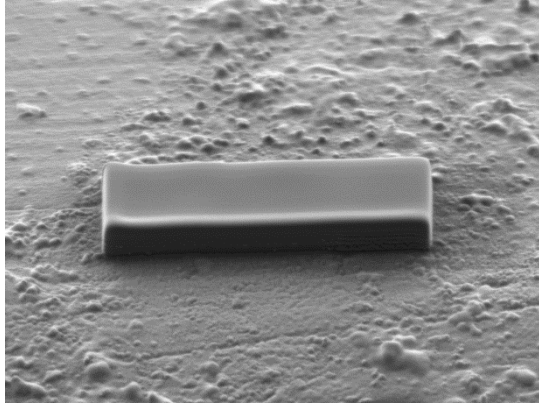
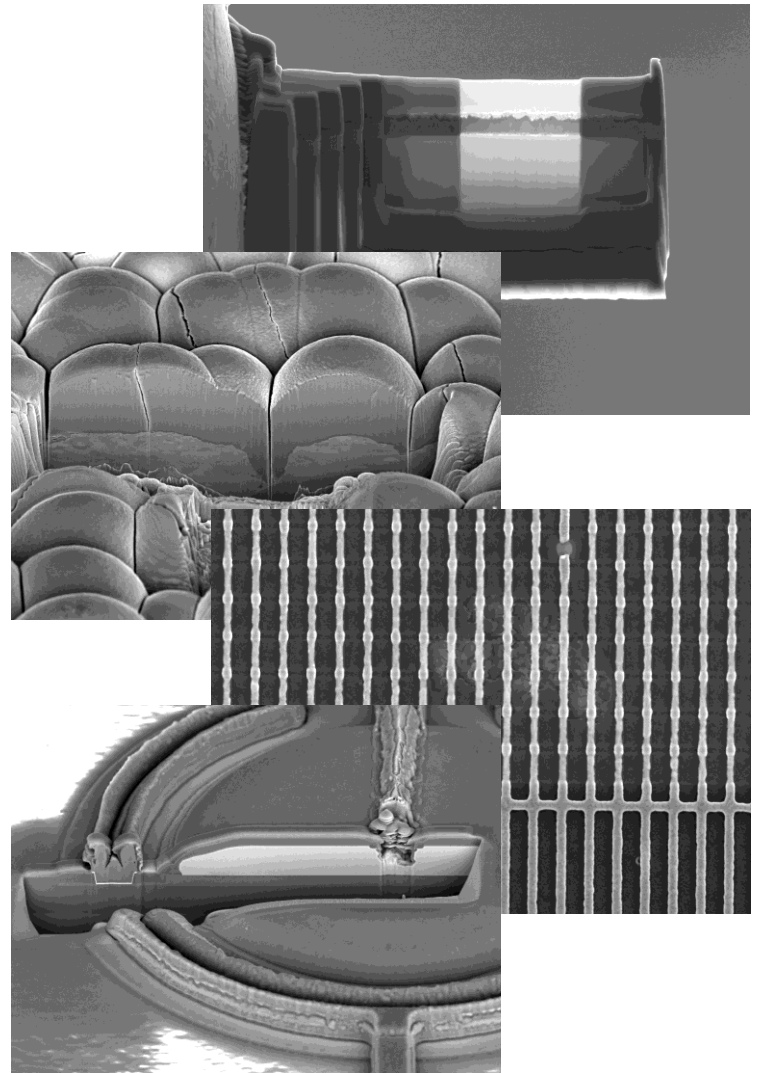


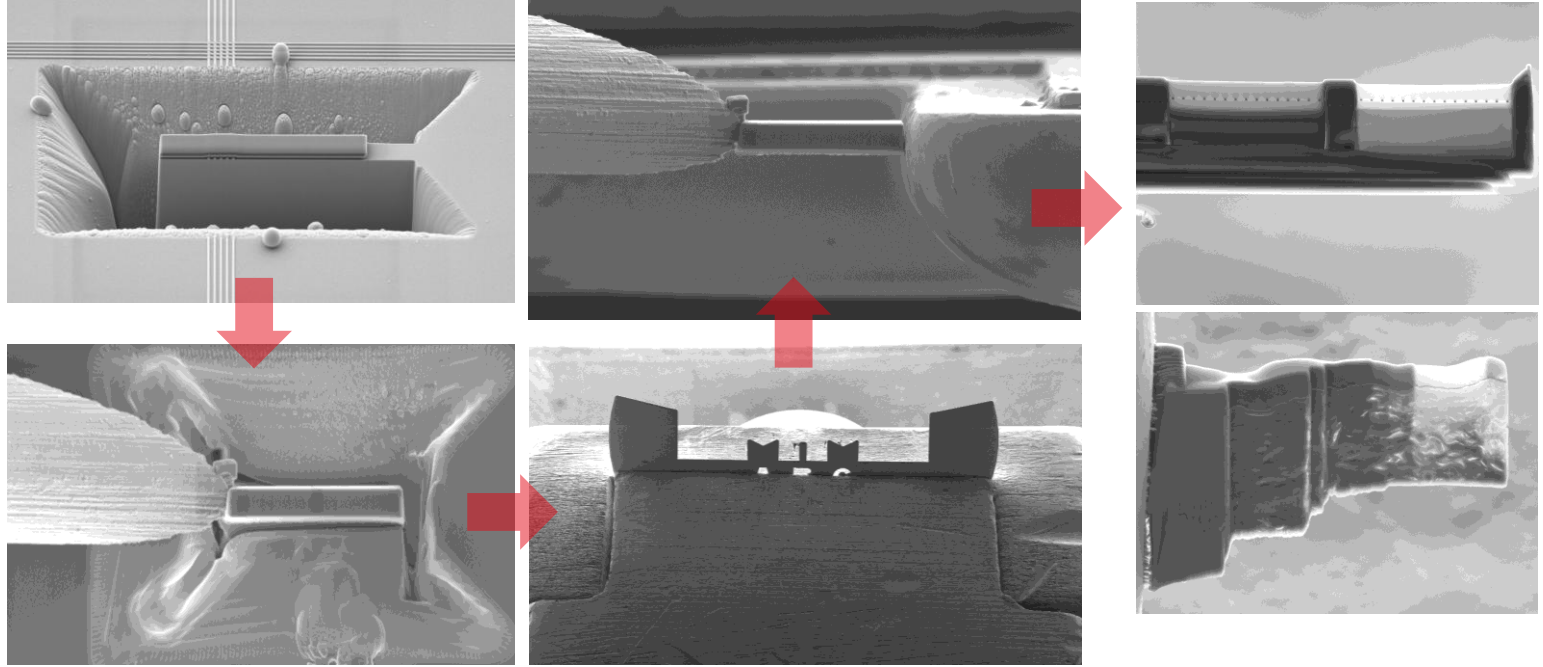
Image source: Orsay Physics

- TEM lamella preparation
 - Precise selection of the position
 - Preparation of heterogenous samples
- 3D nano-tomography
- Failure analysis
- Chip modification
- Nanofabricated structures



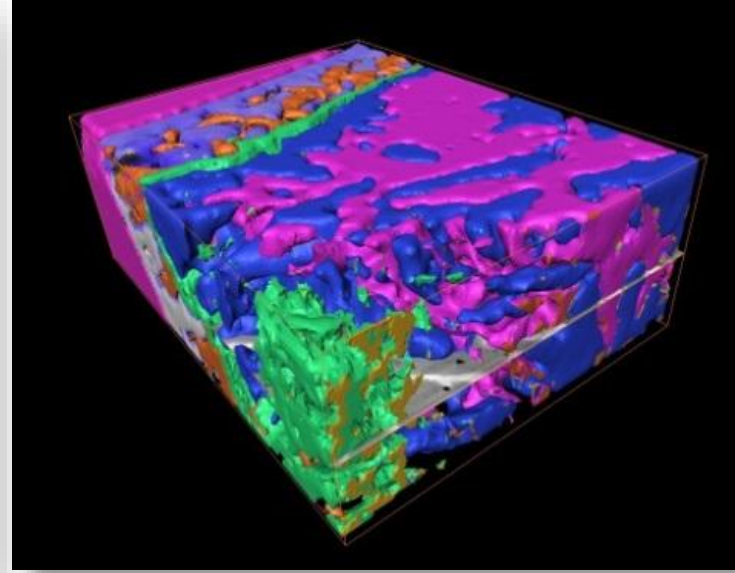
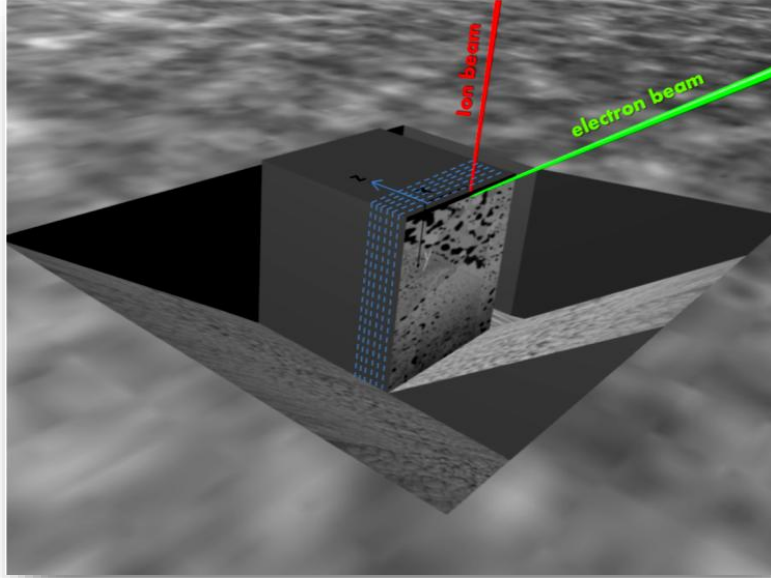
FIB applications

TEM lamella preparation



FIB applications

3D nano-tomography



- SEM – magnified images with better resolution than light microscope
 - Signal: SE, BSE
 - Volume of interaction – low Z vs. high Z, low vs. high acceleration voltage
 - Depth of field – convergence angle
- EDX – chemical composition
 - accuracy is affected by the nature of the sample
- FIB – from 2D SEM to small 3D volume analysis
 - milling, deposition
 - TEM lamella preparation, 3D tomography, nanofabrication



**Thank you for
your attention**